



600V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS} (@ T _J Max)	R _{DS(ON)} Max	I _D T _C = +25°C
650V	2.3Ω @ V _{GS} = 10V	3.7A

Description

This new generation MOSFET has been designed to minimize the onstate resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- **Power Management Functions**

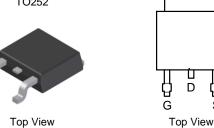
Features

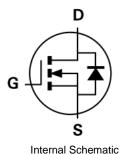
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low Gate Input Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (Approximate)







Ordering Information (Note 4)

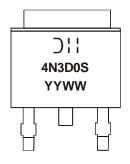
Part Number	Compliance	Case	Packaging
DMG4N60SK3-13	Standard	TO252	2,500/Tape & Reel

D

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃¦¦=Manufacturer's Marking 4N3D0S= Product Type Marking Code YYWW = Date Code Marking YY or YY= Last Digit of Year (ex: 14 = 2014) WW or WW= Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	600	V
Gate-Source Voltage			V _{GSS}	±30	V
Continuous Drain Current, $V_{GS} = 10V$ Steady $T_C = +25^{\circ}C$ State $T_C = +100^{\circ}C$			ID	3.7 2.4	А
Maximum Body Diode Forward Current			I _S	3.7	Α
Pulsed Drain Current (10μs pulse, Duty Cycle = 1%)			I _{DM}	5	Α
Avalanche Current, L = 60mH (Note 6)			I _{AS}	1.7	Α
Avalanche Energy, L = 60mH (Note 6)			E _{AS}	90	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Dawar Discipation	$T_C = +25^{\circ}C$	2	48	W
Total Power Dissipation	T _C = +100°C	P_{D}	19	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	°C/W	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	2.6	C/VV
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

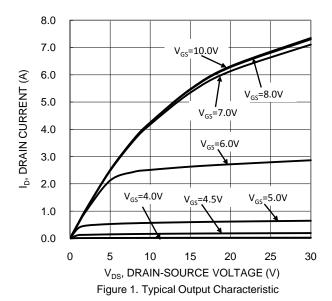
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	600	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 600V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						•
Gate Threshold Voltage	V _{GS(TH)}	2.5	3.5	4.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2.0	2.3	Ω	$V_{GS} = 10V, I_D = 2A$
Diode Forward Voltage	V _{SD}	_	0.8	1.4	V	$V_{GS} = 0V$, $I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	Ciss		532	_		V _{DS} = 25V, f = 1.0MHz, V _{GS} = 0
Output Capacitance	Coss	_	47	_	pF	
Reverse Transfer Capacitance	C _{rss}		4	_		
Gate Resistance	R _G	_	3.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg	_	14.3	_		$V_{DD} = 480V, I_D = 4A,$ $V_{GS} = 10V$
Gate-Source Charge	Q _{gs}	_	3.3	_	nC	
Gate-Drain Charge	Q_{gd}	_	6.9	_		
Turn-On Delay Time	t _{D(ON)}	_	14	_		
Turn-On Rise Time	t _R	_	34	_		$\begin{split} V_{DD} &= 300 \text{V}, \ R_G = 25 \Omega, \ I_D = 4 \text{A}, \\ V_{GS} &= 10 \text{V} \end{split}$
Turn-Off Delay Time	t _{D(OFF)}	_	32	_	ns	
Turn-Off Fall Time	t _F	_	25	_		
Body Diode Reverse Recovery Time	t _{RR}	_	229	_	ns	dl/dt = 100A/µs, V _{DS} = 100V,
Body Diode Reverse Recovery Charge	Q _{RR}	_	1564	_	nC	I _F = 4A

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
- Guaranteed by design. Not subject to production testing.
 Short duration pulse test used to minimize self-heating effect.





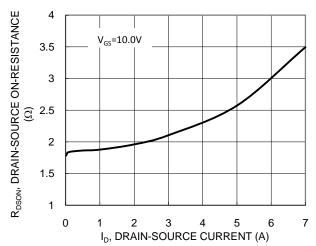


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

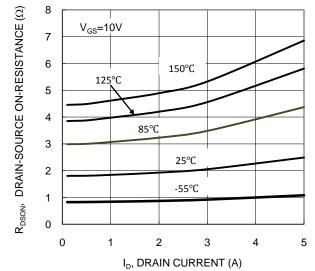


Figure 5. Typical On-Resistance vs Drain Current and Temperature

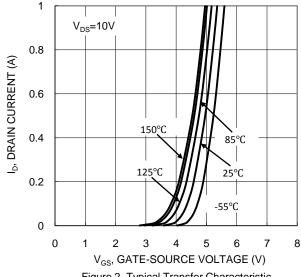


Figure 2. Typical Transfer Characteristic

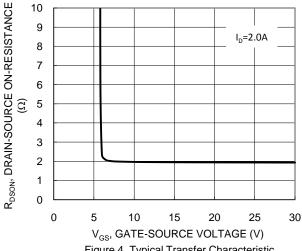


Figure 4. Typical Transfer Characteristic

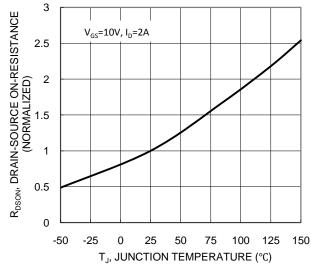


Figure 6. On-Resistance Variation with Temperature



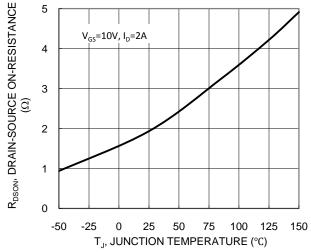
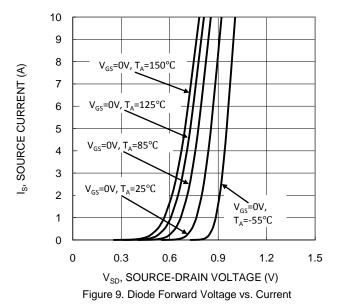
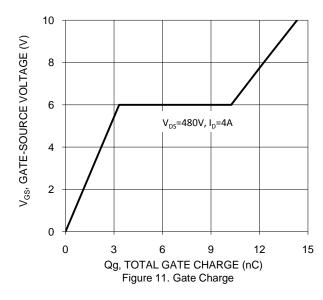


Figure 7. On-Resistance Variation with Temperature





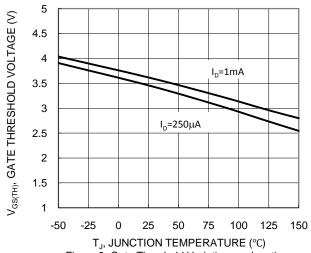


Figure 8. Gate Threshold Variation vs. Junction
Temperature

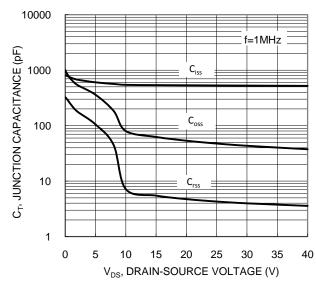
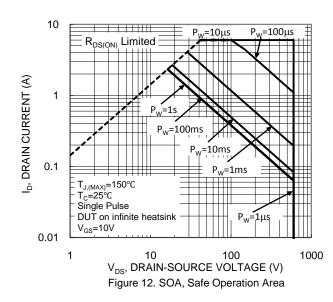
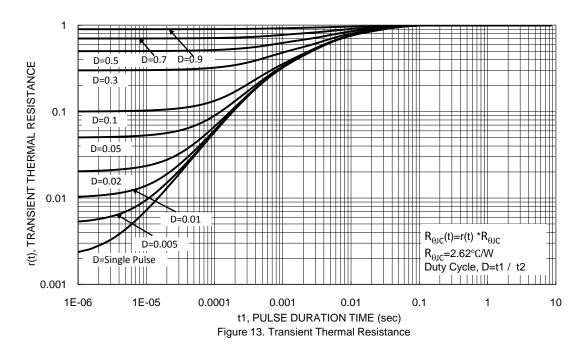


Figure 10. Typical Junction Capacitance



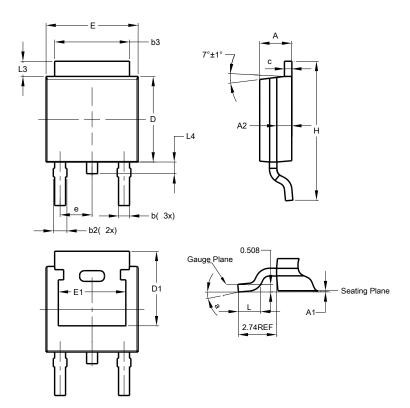




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

(1) Package Type: TO252 (DPAK)



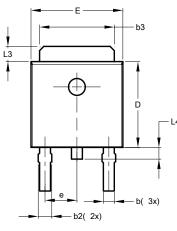
TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
C	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Ξ	9.40	10.41	9.91		
Ь	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

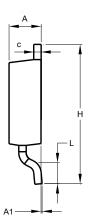


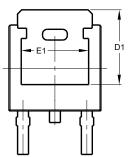
Package Outline Dimensions (Cont.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

(2) Package Type: TO252 (DPAK) (Type BR)

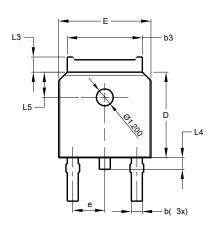


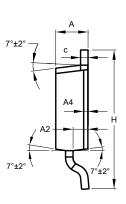


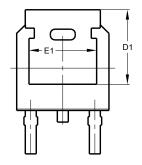


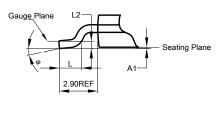
TO252 (DPAK) (Type BR)				
Dim	Min	Max	Тур	
Α	2.20	2.40	- 76	
A1	0.00	0.10	-	
b	0.50	0.70	-	
b3	5.20	5.40	-	
C	0.45	0.55	-	
D	5.95	6.25	-	
D1	5.10	5.50	-	
Е	6.45	6.70	-	
E1	4.71	4.91	-	
е	2.24	2.34		
Н	9.45	9.95	-	
L	1.25	1.75	-	
L3	0.95	1.25	-	
L4	0.60	0.90	-	
All Dimensions in mm				

(3) Package Type: TO252 (DPAK) (Type TH)







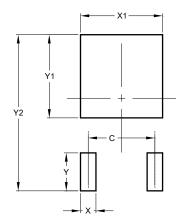


TO252 (DPAK)						
	(Type TH)					
Dim	Min	Max	Тур			
Α	2.20	2.38	2.30			
A 1	0.00	0.10	-			
A2	0.97	1.17	1.07			
A4	0	.10 RE	F			
p	0.72	0.85	0.78			
b3	5.23	5.45	5.33			
С	0.47	0.58	0.53			
D	6.00	6.20	6.10			
D1	5	5.30 REF				
Ф	2.	286 BS	Ö			
Е	6.50	6.70	6.60			
E1	4.70	4.92	4.83			
Н	9.90	10.10	10.30			
L	1.40	1.70	1.60			
L2	0.51 BSC					
L3	0.90	1.25	-			
L4	0.60	1.00	0.80			
L5	1.70	1.90	1.80			
а	0°	8°	-			
All Dimensions in mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Υ	2.600
Y1	5.700
Y2	10.700

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